

EB-4ch VCSEL-5.25-850-50-01



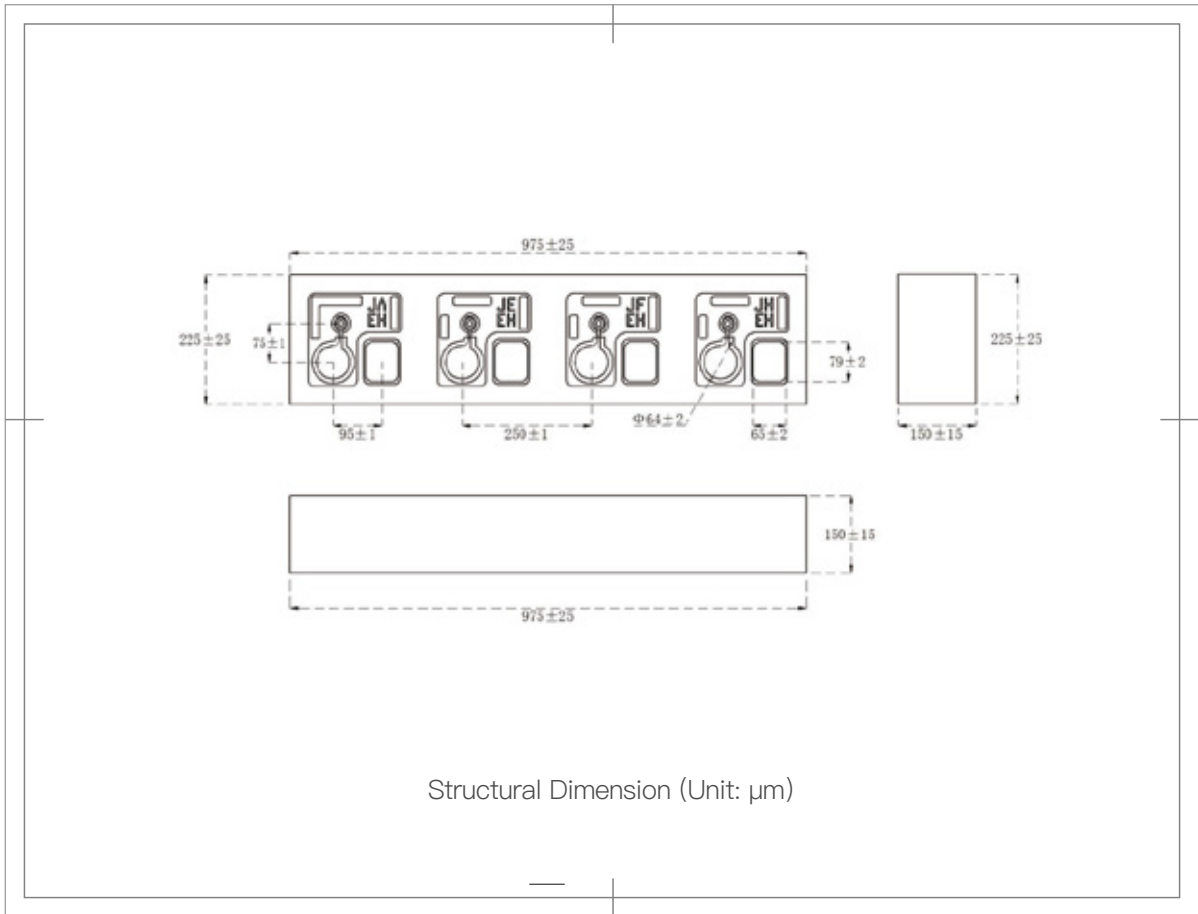
Product Code	Description	Type	Data Rate	Operating Temperature
EB-1ch VCSEL-5.25-850-50-01	50G PAM4 VCSEL	Single Chip	50G	5~75°C
EB-2ch VCSEL-5.25-850-50-01	1 x 2 50G PAM4 VCSEL Array	Array, 1*2	50G	5~75°C
EB-4ch VCSEL-5.25-850-50-01	1 x 4 50G PAM4 VCSEL Array	Array, 1*4	50G	5~75°C

Characteristics



	Unit	Min	Typical	Max	Notes
Average Operating Current	mA			7.5	$T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Threshold Current	mA	0.2		1.5	$T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Output Power	mW	2		4.7	$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Slope Efficiency	W/A		0.45		$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Forward Voltage	V			2.5	$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Series Resistance	Ohm	50		80	$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Center Wavelength	nm	840	850	860	$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Center Wavelength Temperature Variation	nm/°C		0.065		
Spectral Width (RMS)	nm		0.4	0.6	$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Small Signal Modulation Bandwidth	GHz		19		$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$
Relative Intensity Noise	dB/Hz		-146	-140	$I_f = 7.5 \text{ mA}, T_s = 5^{\circ}\text{C} \sim 75^{\circ}\text{C}$

Remarks




- Explanation of Item Number: EB (Everbright in short)–4ch VCSEL(Vertical–Cavity Surface–Emitting Laser)–5.25(Power dBm)–850(Wavelength)–50(Date Rate 为 50Gbps)–01(Version Number)
- It is a 150um thick, 850 nm wavelength, GaAs–based vertical cavity surface emitting laser (VCSEL) array that is designed for 200/400 Gbps Ethernet optical links on multimode fiber.
- When used under extreme operating conditions, it will cause permanent damage to the chip.
- Long–term use under near–limit operating conditions may adversely affect product performance and life.
- Normal ESD precautions are required during the handling of this chip. This chip is shipped in ESD protective packaging. It should be removed from the packaging and otherwise handled in an ESD protected environment utilizing standard grounded benches, floor mats, and wrist straps.



Applications

-  50G/200G/400G Ethernet
-  200G to 100G Breakout

Features

-  High Bandwidth
-  Narrow Spectral Width
-  Low RIN



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